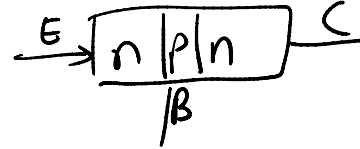


LECTURE - 24

npn TRANSISTOR

SUMMARY → DESIGN OPTIMIZATION



①

$n+$

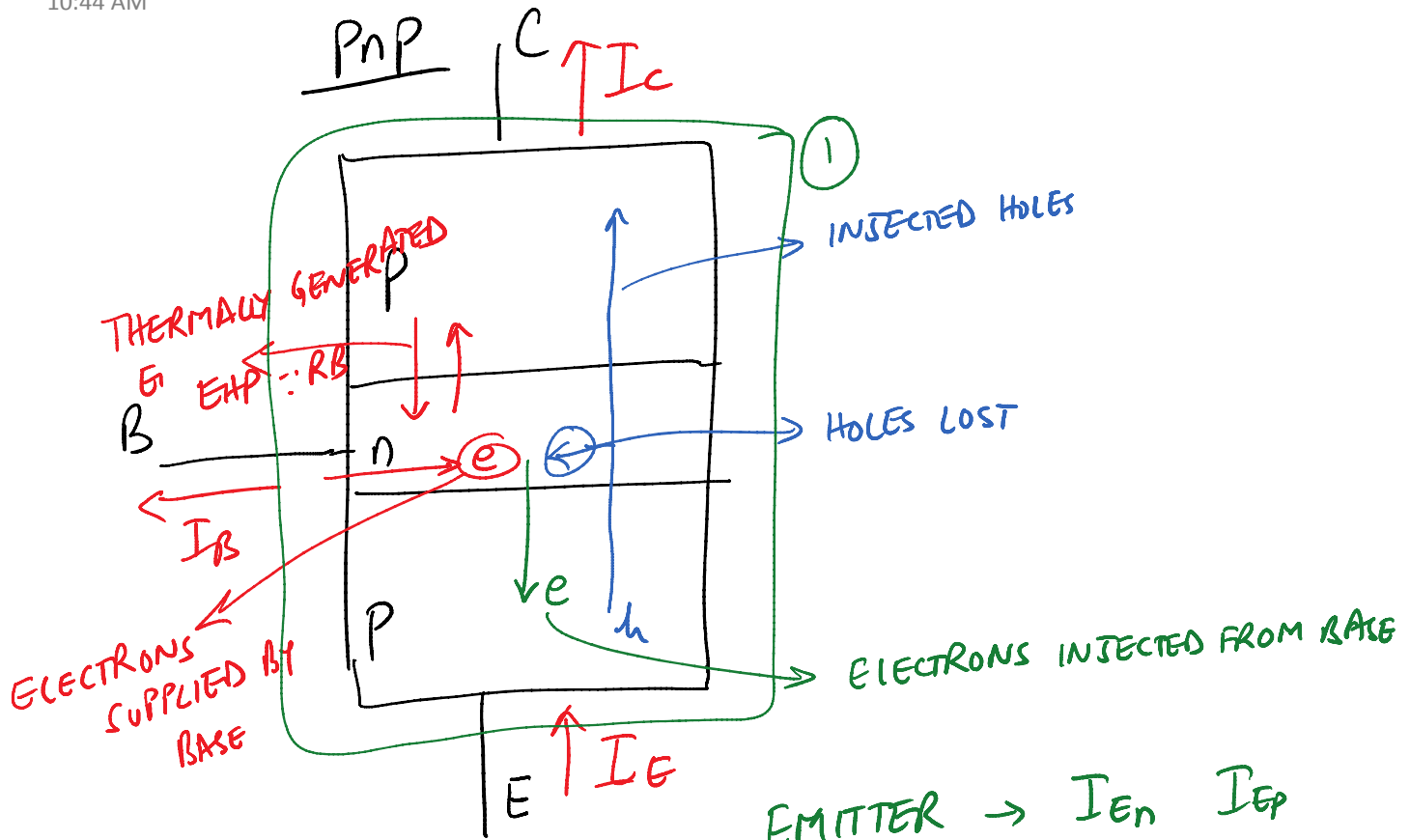
$$I_E \approx I_{En}$$

$$\gamma = \frac{I_{En}}{I_{En} + I_{Ep}}$$

NEAR UNITY

②

NARROW BASE WIDTH, LIGHT BASE DOPING
 $\alpha_F \rightarrow$ NEAR UNITY!



EMITTER $\rightarrow I_{En} \quad I_{Ep}$
 COLLECTOR $\rightarrow I_c \approx I_{cp}$
 BASE $\rightarrow I_b \approx I_{bn}$

$$\gamma = \frac{I_{Ep}}{I_{Ep} + I_{En}}$$

$$\alpha_F = \frac{I_{cp}}{I_{Ep}}$$

$$\alpha = \alpha_0 = \frac{I_c}{I_E} = \alpha_F \gamma$$

KCL NODE 1

$$-I_E + I_B + I_C = 0$$

$$I_B = I_E - I_C$$

$$\beta = \frac{I_C}{I_B} = \frac{\alpha}{1 - \alpha} \quad \alpha = \frac{\beta}{1 + \beta}$$

DESIGN OPTIMIZATION CRITERIA

PNP

$$P^+ \quad I_E \approx I_{EP}$$

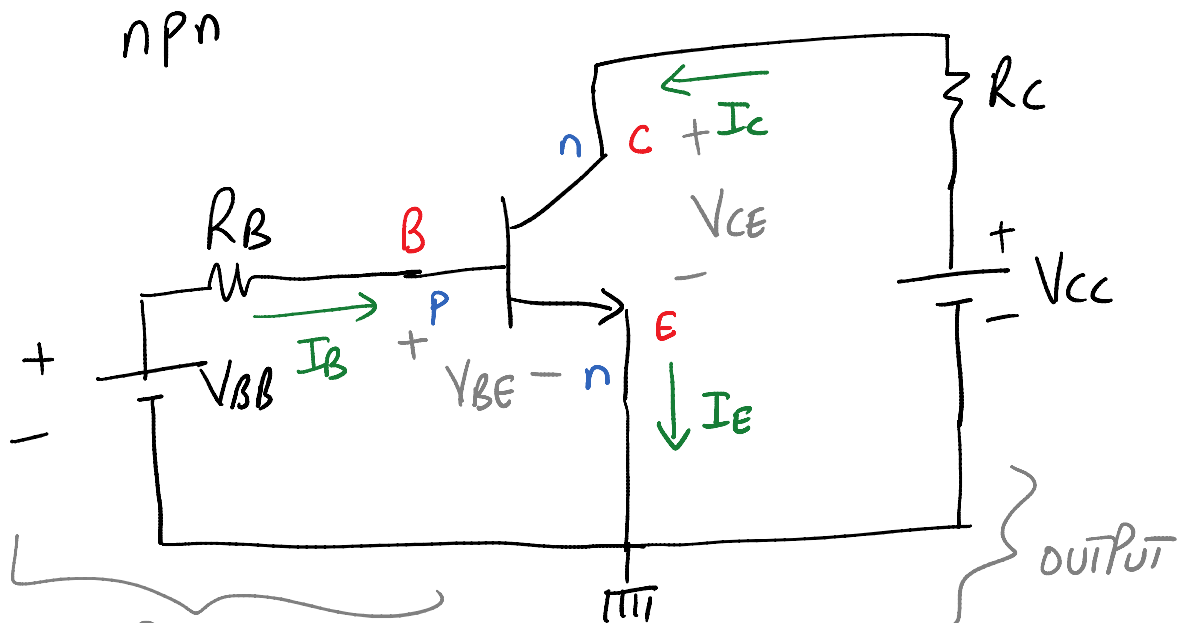
$$\gamma = \frac{I_{EP}}{I_{EP} + I_{EN}} \quad \text{NEAR UNITY}$$

NARROW BASE & WIDTH, LIGHT BASE DOPING!

CIRCUIT CONFIGURATIONS

- ① COMMON EMITTER
 - ② COMMON COLLECTOR / EMITTER FOLLOWER
 - ③ COMMON BASE
- CHOICE BASED ON APPLICATION

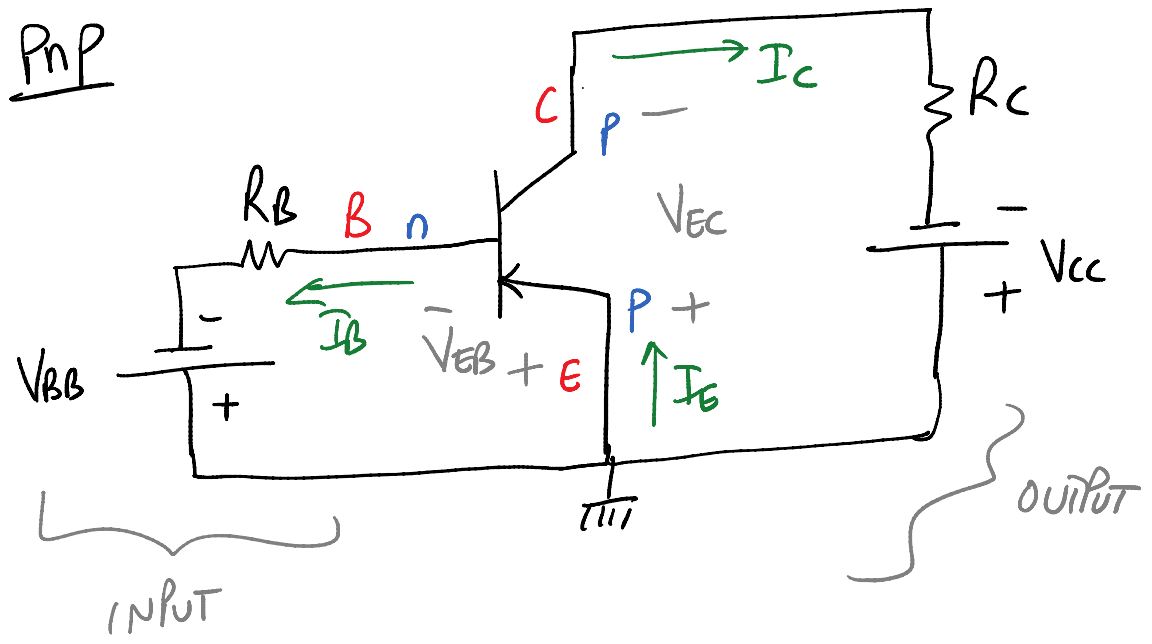
COMMON EMITTER



FOR FORWARD BIASING
"ACTIVE REGION"

BE \rightarrow FB
CE \rightarrow RB

Wednesday, February 06, 2013
10:54 AM



CURRENT AMPLIFICATION GAIN

$$\beta = \frac{I_c}{I_b}$$

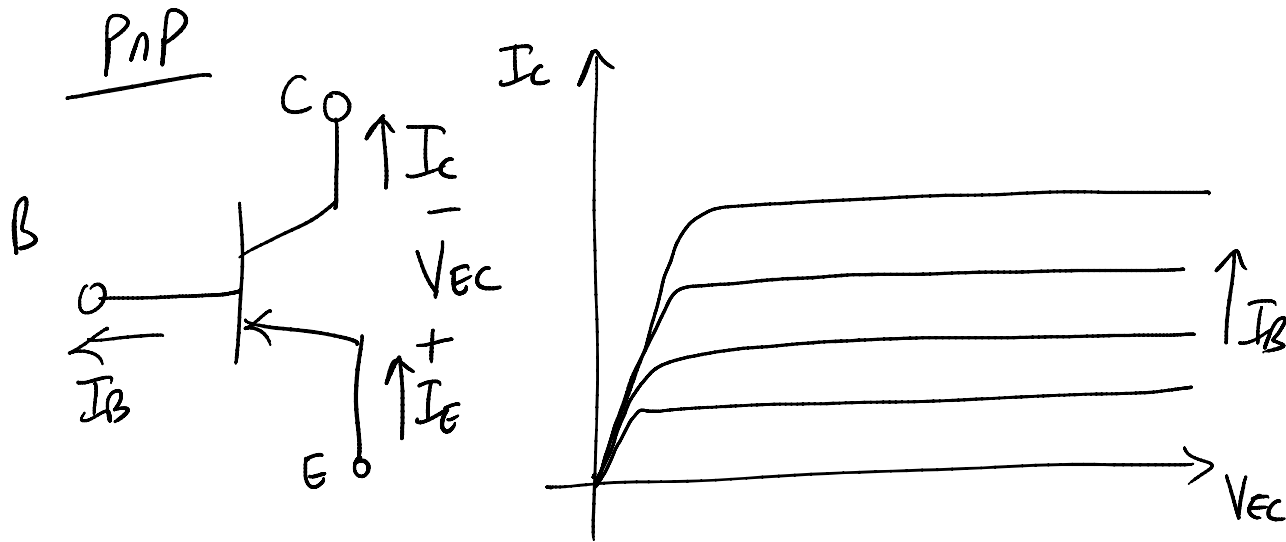
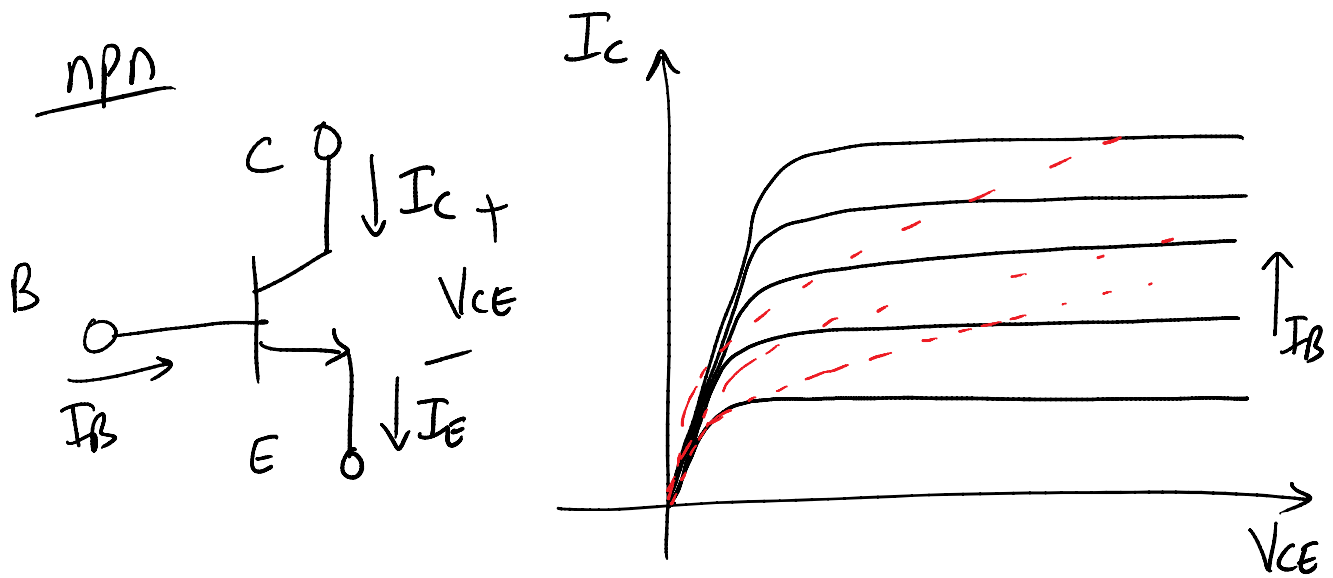
ONLY VALID FOR
FORWARD ACTIVE REGION

i.e. WHEN ANALYZING ~~THE~~ A
CIRCUIT AND GOING FROM INPUT
SIDE TO OUTPUT SIDE

3 BASIC REGIONS OF OPERATION

- ① CUTOFF
- ② FORWARD ACTIVE "ACTIVE"
- ③ SATURATION

IV CHARACTERISTICS



THINGS TO REMEMBER

① FOR CUT-OFF V_{BE} (OR V_{EB}) $< V_{to}$
 $I_B \approx 0$ $I_C \approx 0$
(TURN-ON VOLTAGE FOR PN JUNCTION)

② FOR V_{BE} (OR V_{EB}) $> V_{to}$
AND V_{CE} (OR V_{EC}) $< V_{CE}$ (OR V_{EC})
(SATURATION)

SPECIFICATION FOUND IN DATASHEET

ACTIVE REGION

③ IF V_{CE} (OR V_{EC}) $\leq V_{CE}$ (OR V_{EC})
(SAT)
THEN SATURATION REGION